



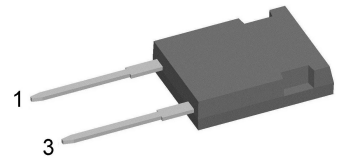
HiPerDynFRED

$V_{RRM} = 1200\text{ V}$
 $I_{FAV} = 30\text{ A}$
 $t_{rr} = 15\text{ ns}$

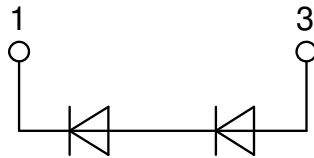
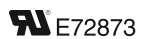
High Performance Dynamic Fast Recovery Diode
 Extreme Low Loss and Soft Recovery
 Single Diode

Part number

DSEP30-12CR



Backside: isolated



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: ISOPLUS247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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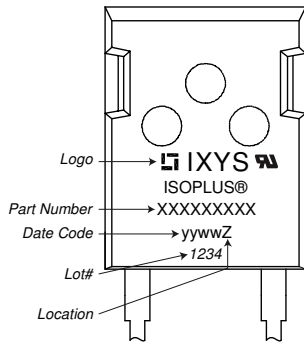


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage				1200	V	
V_{RRM}	max. repetitive reverse blocking voltage				1200	V	
I_R	reverse current, drain current	$V_R = 1200\text{ V}$			250	μA	
		$V_R = 1200\text{ V}$			2	mA	
V_F	forward voltage drop	$I_F = 30\text{ A}$			4.98	V	
		$I_F = 60\text{ A}$			6.33	V	
		$I_F = 30\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			3.18	V
		$I_F = 60\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			4.40	V
I_{FAV}	average forward current	$T_C = 105^\circ\text{C}$ rectangular $d = 0.5$			30	A	
V_{FO}	threshold voltage	} for power loss calculation only			1.69	V	
r_F	slope resistance				36.6	m Ω	
R_{thJC}	thermal resistance junction to case				0.6	K/W	
R_{thCH}	thermal resistance case to heatsink			0.3		K/W	
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		250	W	
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^\circ\text{C}$		250	A	
C_J	junction capacitance	$V_R = 800\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		13	pF	
I_{RM}	max. reverse recovery current	} $I_F = 30\text{ A}; V_R = 600\text{ V}$ $-di_F/dt = 600\text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		5.5	A	
			$T_{VJ} = 100^\circ\text{C}$		12.5	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^\circ\text{C}$			15	ns
			$T_{VJ} = 100^\circ\text{C}$			70	ns



Package ISOPLUS247		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	5.4			mm
$d_{Spb/Apb}$		terminal to backside	4.1			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

Product Marking



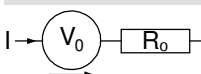
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP30-12CR	DSEP30-12CR	Tube	30	481955

Similar Part	Package	Voltage class
DSEP30-12A	TO-247AD (2)	1200
DSEP29-12A	TO-220AC (2)	1200
DSEP30-12AR	ISOPLUS247 (2)	1200
DHG30I1200HA	TO-247AD (2)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}C$

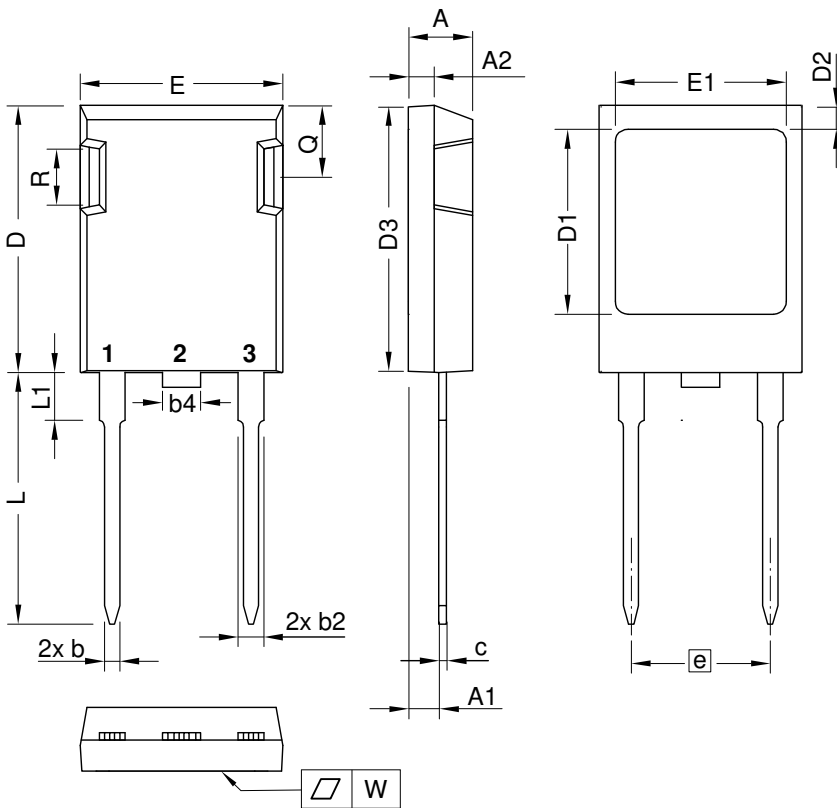


Fast Diode

$V_{0\ max}$	threshold voltage	1.69	V
$R_{0\ max}$	slope resistance *	34	mΩ



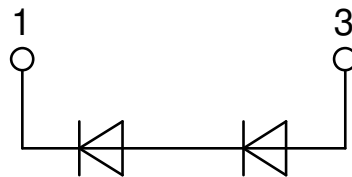
Outlines ISOPLUS247



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	10.90 BSC		0.429 BSC	
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max}.
This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except L_{max}.



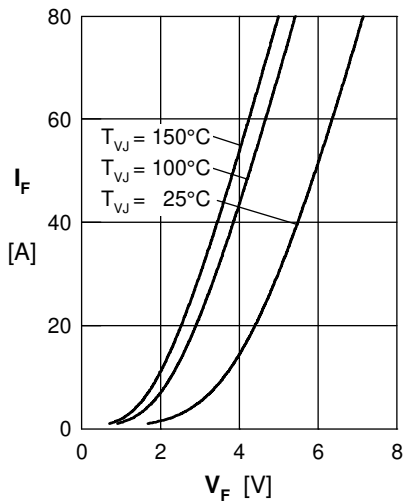
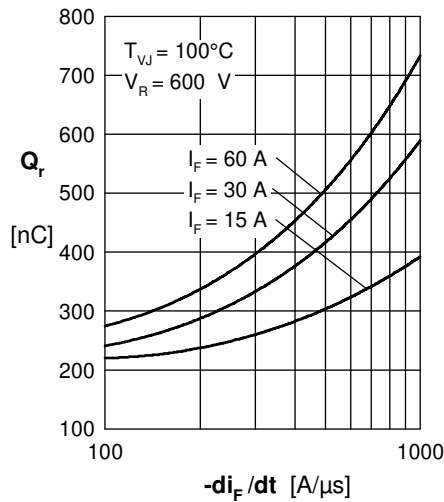
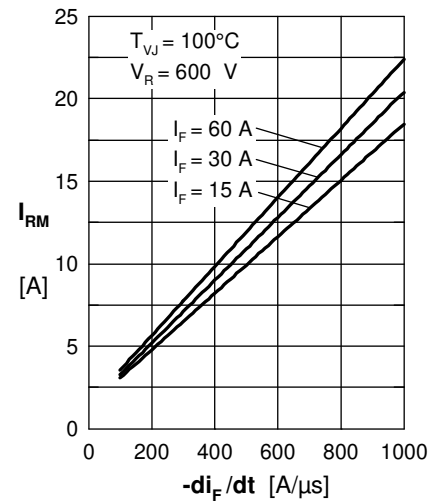
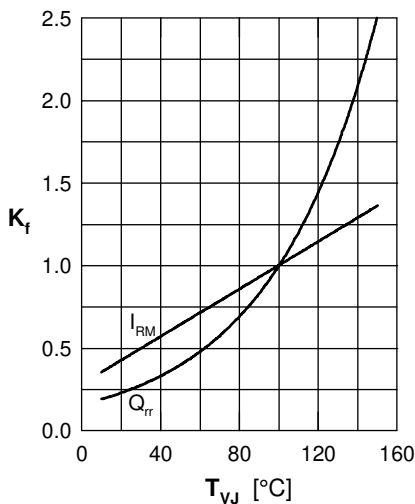
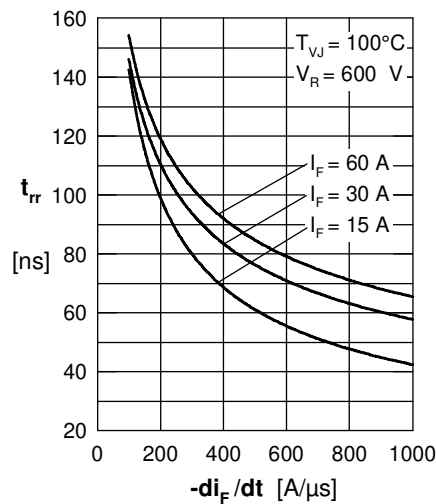
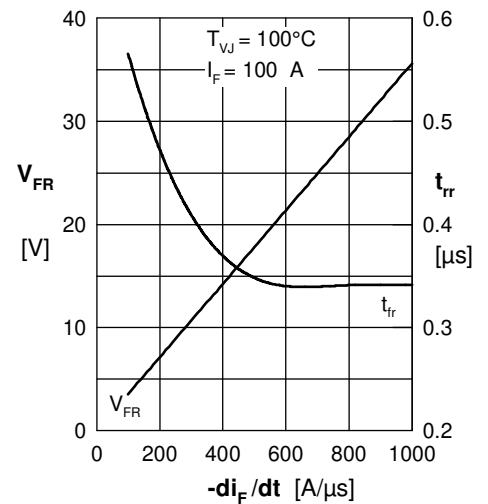
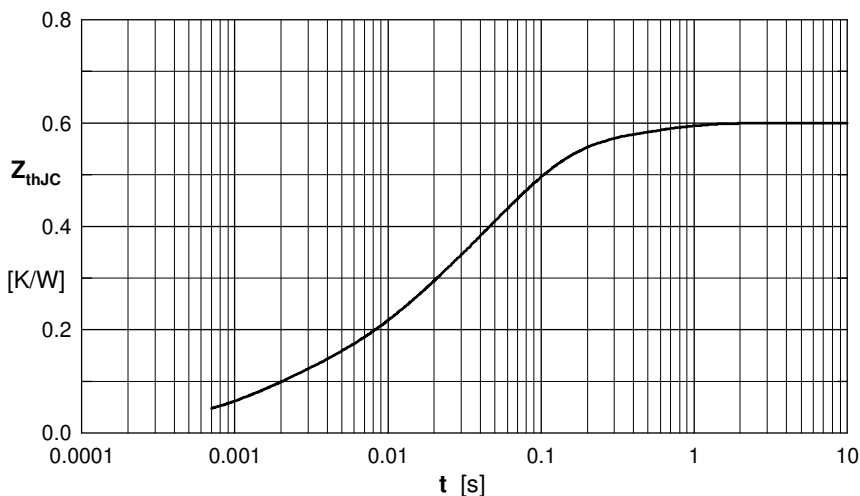
Fast Diode

 Fig. 1 Forward current I_F vs. V_F

 Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

 Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

 Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt


Fig. 7 Transient thermal resistance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.08	0.0013
2	0.122	0.0097
3	0.116	0.037
4	0.23	0.07
5	0.052	0.45